

AMENDMENTS TO THE CLAIMS:

1. (Currently amended) A thick film photoresist composition comprising:

(A) a resin component containing (a) from 61 to 90% by weight of a structural unit derived from a cyclic alkyl (meth)acrylate ester, and (b) a structural unit derived from a radical polymerizable compound containing a hydroxyl group[.,,];

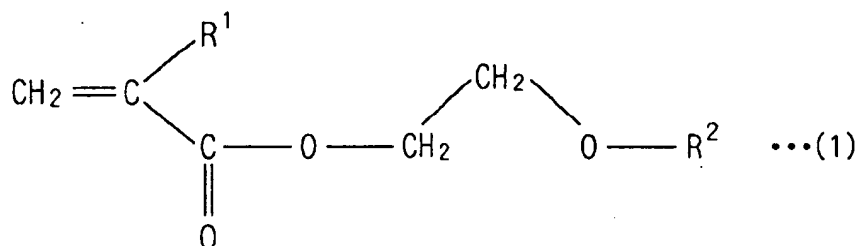
(B) a polymerizable compound containing at least one ethylenic unsaturated double bond[.,,];

(C) a photopolymerization initiator[.,,]; and

(D) an organic solvent.

2. (Original) A thick film photoresist composition according to claim 1, wherein said structural unit (b) accounts for at least 1% by weight, but less than 10% by weight, of said component (A).

3. (Original) A thick film photoresist composition according to claim 1, wherein said component (A) further comprises (c) a structural unit derived from a radical polymerizable compound represented by a general formula (1) shown below:



(wherein, R<sup>1</sup> represents a hydrogen atom or a methyl group, and R<sup>2</sup> represents a hydrogen atom or an alkyl group of 1 to 4 carbon atoms).

4. (Currently amended) A thick film photoresist composition according to claim 1, wherein said component (D) is ~~at least one solvent selected from a group consisting of~~ methyl isobutyl ketone ~~and~~ and/or methyl ethyl ketone.
5. (Original) A method of forming a resist pattern, wherein said resist pattern is formed using a thick film photoresist composition according to any one of claim 1 through claim 4.
6. (Currently amended) A pattern formed using said ~~the~~ method ~~disclosed in~~ according to claim 5.